

BIPOLAR NALOG NTEGRATED IRCUIT

 μ PC2726T

1.6 GHz DIFFERENTIAL WIDE BAND AMPLIFIER SILICON BIPOLAR MONOLITHIC INTEGRATED CIRCUIT

DESCRIPTION

The μ PC2726T is a silicon microwave monolithic integrated circuit designed for miniature differenctial amplifier. This IC operates up to 1.6 GHz and therefore is suitable for BS tuner, mobile communication and measurement equipment applications. This IC can also use as differential oscillator application.

The μ PC27 \times x series is manufactured using NEC's 20 GHz fr NESATTM III silicon bipolar process. This process uses silicon nitride passivation film and gold metallization wirings. These materials can protect the chips from external pollution and prevent corrosion and migration. Thus, this process can produce the ICs with excellent performance, uniformity and reliability.

FEATURES

- Wide frequency respone f_U = 1.6 GHz @ -3 dB G_P , V_{CC} = 5 V
- Power gain GP = 15 dB @ 5 V
- Low power consumption: 5 V, 15 mA TYP./2 V, 2.5 mA
- · 6 pin mini mold for high-density surface mounting.

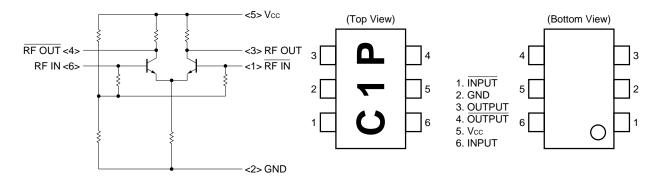
ORDERING INFORMATION

PART NUMBER	PACKAGE	SUPPLYING FORM		
μPC2726T-E3	6 pin mini mold	Embossed tape 8 mm wide. 3 kp/reel. Pin 1, 2, 3 face to perforation side of the tape.		

^{*} For evaluation sample order, please contact your local NEC sales office. (Part number: μ PC2726T)

EQUIVALENT CIRCUIT

PIN CONNECTIONS



Caution: Electro-static sensitive device



ABSOLUTE MAXIMUM RATINGS

Supply Voltage Vcc 6 V $T_A = +25$ °C

Power Dissipation of Package Allowance P_D 280 mW Mounted on $50 \times 50 \times 1.6$ mm

epoxy glass

PWB at $T_A = +85 \,^{\circ}\text{C}$

Input Power P_{in} 0 dBm $T_A = +25$ °C

 $\begin{array}{cccc} \text{Operating Temperature} & & & T_{\text{opt}} & -40 \text{ to } +85 & \text{ }^{\circ}\text{C} \\ \text{Storage Temperature} & & & T_{\text{stg}} & -55 \text{ to } +150 & \text{ }^{\circ}\text{C} \\ \end{array}$

RECOMMENDED OPERATING CONDITIONS

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	Vcc	4.5	5.0	5.5	٧
Operating Temperature	TA	-40	+25	+85	°C

ELECTRICAL CHARACTERISTICS (TA = +25 °C, Vcc = 5. V, ZL = Zs = 50 Ω)

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Circuit Current	Icc	8.0	11.5	15.0	mA	No input signal
Power Gain	G₽	11.0	15	17.0	dB	f = 400 MHz
Noise Figure	NF		4.5	6.0	dB	f = 400 MHz
Upper Limit Operating Frequency	fυ	1.0	1.6		GHz	3 dB down below flat gain at 0.4 GHz
Isolation	ISL		60		dB	f = 400 MHz
Input Return Loss	RLin		2.0		dB	f = 400 MHz
Output Return Loss	RLout		4.0		dB	f = 400 MHz
Maximum Output Level	P _{O(sat)}	-5	-2		dBm	f = 400 MHz, P _{in} = -10 dBm

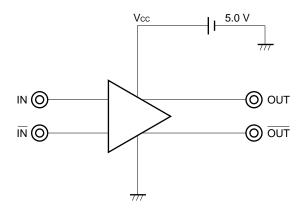
STANDARD CHARACTERISTICS FOR REFERENCE (TA = +25 °C, ZL = Zs = 50 Ω)

PARAMETERS	SYMBOL	REFERENCE VALUE	UNIT	TEST CONDITIONS	
Circuit Current	Icc	2.5	mA	Vcc = 2 V, No input signal	
Power Gain	G₽	4.5	dB	Vcc = 2 V, f = 400 MHz	
Noise Figure	NF	5.1	dB	Vcc = 2 V, f = 400 MHz	
Upper Limit Operating Frequency	fu	2.4	GHz	3 dB down below flat gain at 0.4 GHz	
Isolation	ISL	58	dB	Vcc = 2 V, f = 400 MHz	
Input Return Loss	RLin	1.0	dB	Vcc = 2 V, f = 400 MHz	
Output Return Loss	RLout	4.0	dB	Vcc = 2 V, f = 400 MHz	
Maximum Output Power	Po(sat)	-14	dBm	Vcc = 2 V, f = 400 MHz, P _{in} = -10 dBm	
3rd Order Intermodulation Distortion	IМз	-29	dBc	$Vcc = 2 \text{ V}, \text{ Po}_{(each)} = -25 \text{ dBm}, \text{ f}_1 = 400 \text{ MHz}, \\ f_2 = 402 \text{ MHz}$	
3rd Order Intermodulation Distortion	IMз	-45	dBc	$Vcc = 5 \text{ V}, \text{ Po}_{\text{(each)}} = -25 \text{ dBm}, \text{ f}_1 = 400 \text{ MHz}, \\ \text{f}_2 = 402 \text{ MHz}$	

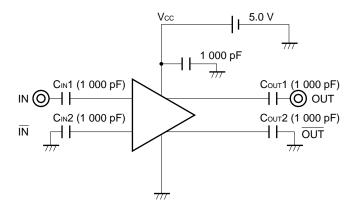


TEST CIRCUITS

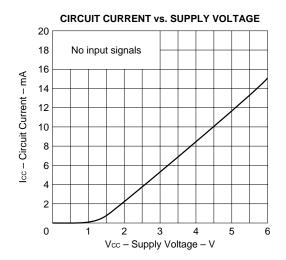
DC Parameters

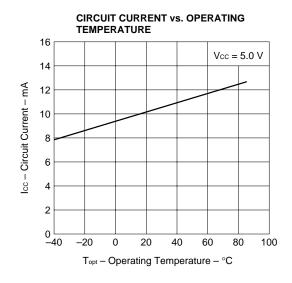


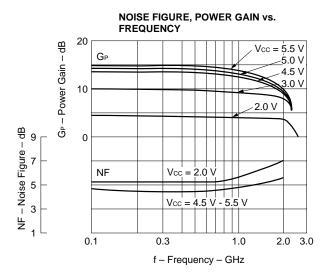
AC Parameters

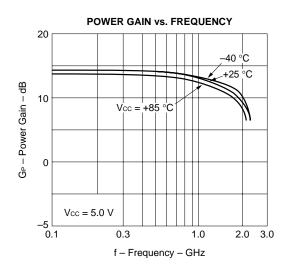


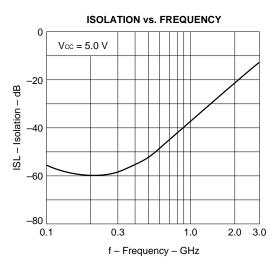
TYPICAL CHARACTERISTICS (Unless otherwise specified T_A = +25 °C)

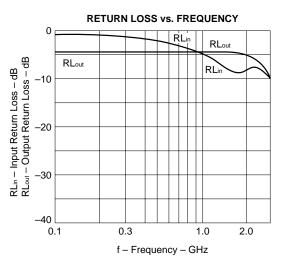


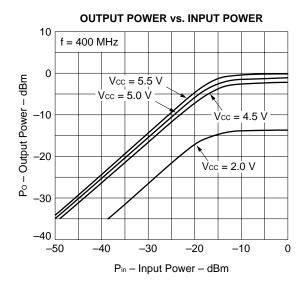


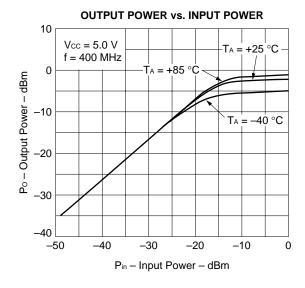


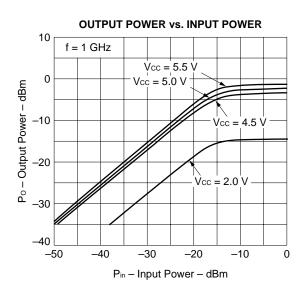


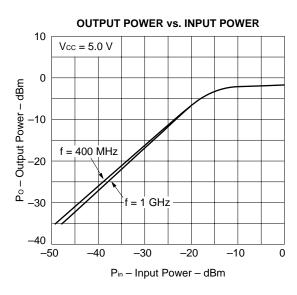


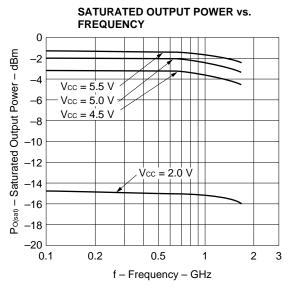


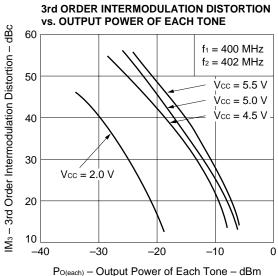






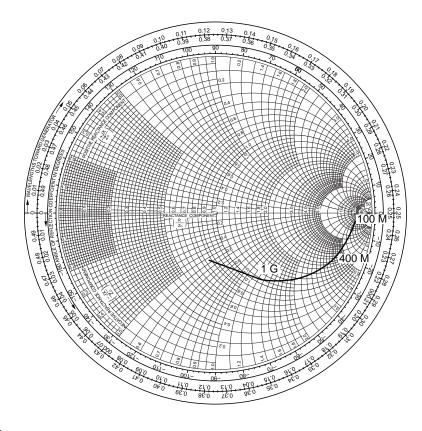






S PARAMETER

S₁₁-FREQUENCY



S22-FREQUENCY

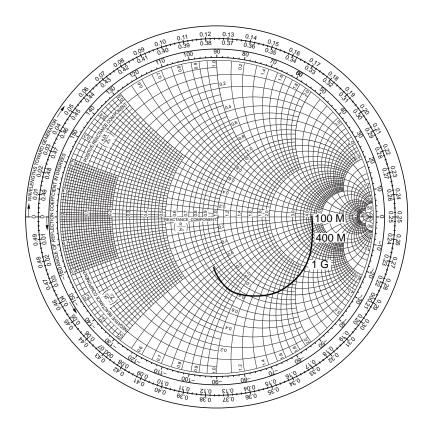
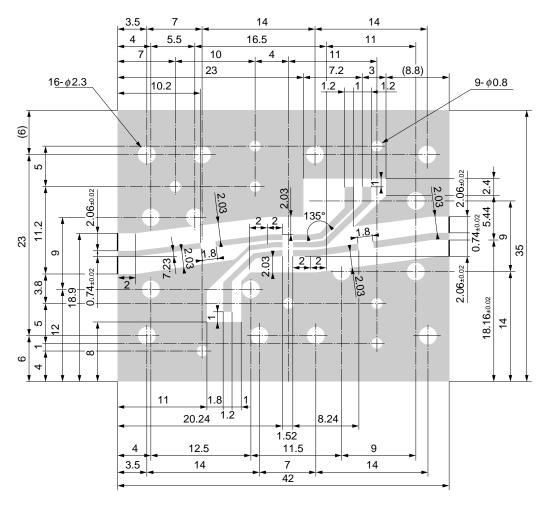
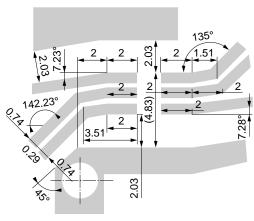




ILLUSTRATION OF THE EVALUATION BOARD FOR TEST CIRCUIT





t = 0.4

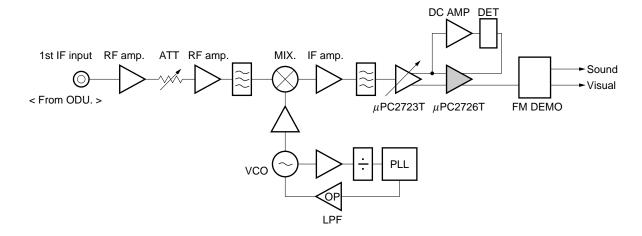
DETAIL LAYOUT

Note

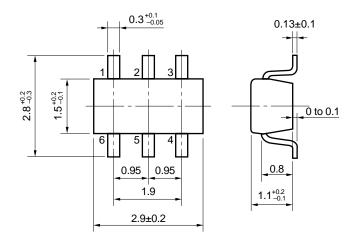
- (1) $50 \times 50 \times 0.5$ mm double copper clad polyimide board.
- (2) Back side: GND pattern
- (3) Solder plated on pattern
- (4) ∘O: Through holes

EXAMPLE FOR SYSTEM APPLICATION

DBS tuner



6 PINS MINI MOLD PACKAGE DIMENSIONS (Unit: mm)





NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as wide as possible to prevent an increase in ground impedance (which can cause undesired oscillation).
- (3) Keep the wiring length of the ground pins as short as possible.
- (4) Connect a bypass capacitor (having, for example, a capacitance of 1 000 pF) to the Vcc pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered in the following recommended conditions. Other soldering methods and conditions than the recommended conditions are to be consulted with our sales representatives.

μ PC2726T

Soldering process	Soldering conditions	Recommended condition symbols
Infrared ray reflow	Package peak temperature: 235 °C, Hour: within 30 s. (more than 210 °C), Time: 3 times, Limited days; no.*	IR35-00-3
VPS	Package peak temperature: 215 °C, Hour: within 40 s. (more than 200 °C), Time: 3 times, Limited days: no.*	VP15-00-3
Wave soldering	Soldering tub temperature: less than 260 °C, Hour: within 10 s. Time: 1 time, Limited days: no.	WS60-00-1
Pin part heating	Pin area temperature: less than 300 °C, Hour: within 3 s. Limited days: no.*	

^{*:} It is the storage days after opening a dry pack, the storage conditions are 25 °C, less than 65 % RH.

Note 1. The combined use of soldering method is to be avoided (However, except the pin area heating method).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).

[MEMO]

The application circuit and circuit constants shown in this document are for reference only and may not be employed for mass production of the application system.

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Anti-radioactive design is not implemented in this product.

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